

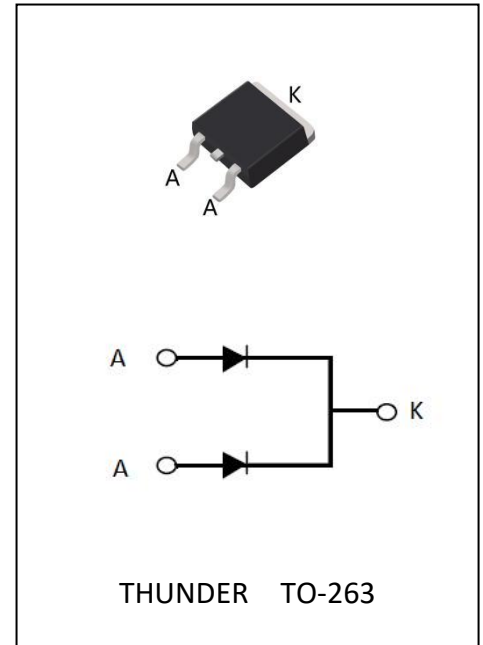
FRED

Ultrafast Soft Recovery Diode, 8A

Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I_R value
- High surge capacity
- Epitaxial chip construction

Product Summary	
V_R	1200V
$I_{F(AV)}$	8A
t_{rr}	30ns


Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

Absolute Maximum Ratings

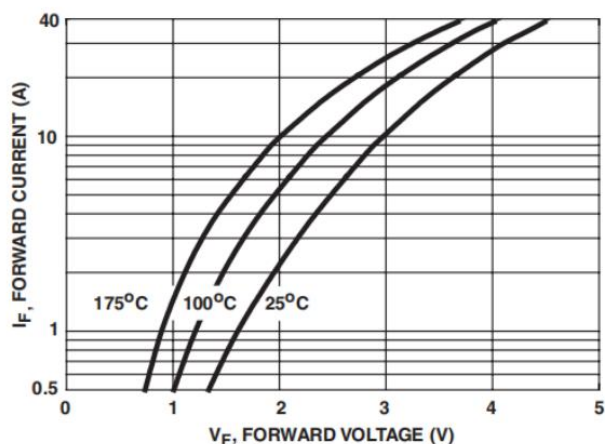
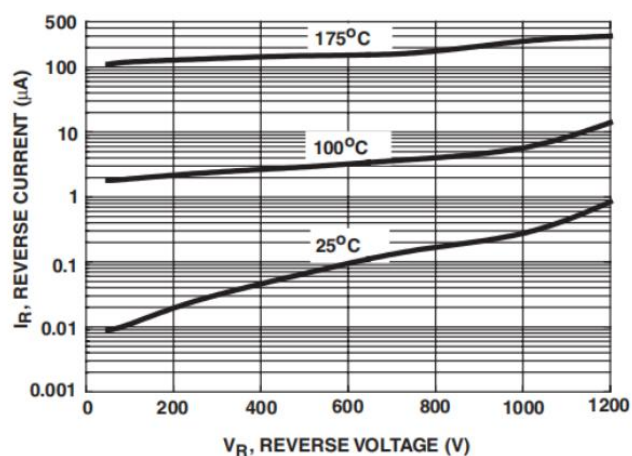
Parameter	Symbol	Test Conditions	Values	Unit
Repetitive peak reverse voltage	V_{RRM}		1200	V
Continuous forward current	$I_{F(AV)}$	$T_c = 110^\circ\text{C}$	8	A
Single pulse forward current	I_{FSM}	$T_c = 25^\circ\text{C}$	80	
Maximum repetitive forward current	I_{FRM}	Square wave, 20kHz	16	
Operating junction	T_j		175	$^\circ\text{C}$
Storage temperatures	T_{stg}		-55 to +175	$^\circ\text{C}$

Electrical characteristics (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Breakdown voltage Blocking voltage	V_{BR} , V_R	$I_R=100\mu A$	1200			V
Forward voltage (Per Diode)	V_F	$I_F=8A$		2.10	2.50	
		$I_F=8A, T_j=125^\circ C$		1.95	2.50	
Reverse leakage current(Per Diode)	I_R	$V_R=V_{RRM}$			20	μA
		$T_j=150^\circ C, V_R=1200V$			200	
Reverse recovery time(Per Diode)	t_{rr}	$I_F=0.5A, I_R=1A, I_{RR}=0.25A$		30	40	ns

Thermal characteristics

Paramter	Symbol	Typ.	Unit
$R_{\theta JC}$	Junction-to-Case	3.0	$^\circ C/W$

Electrical performance (typical)

FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

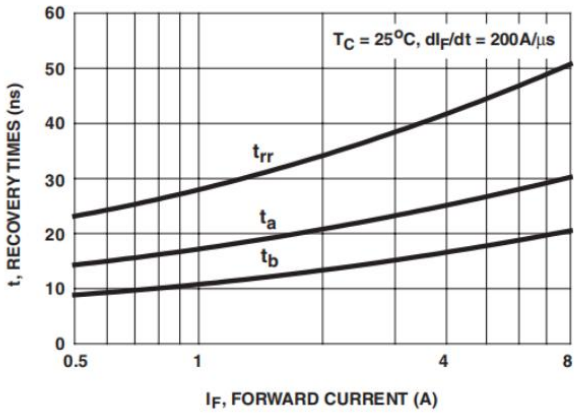


FIGURE 3. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

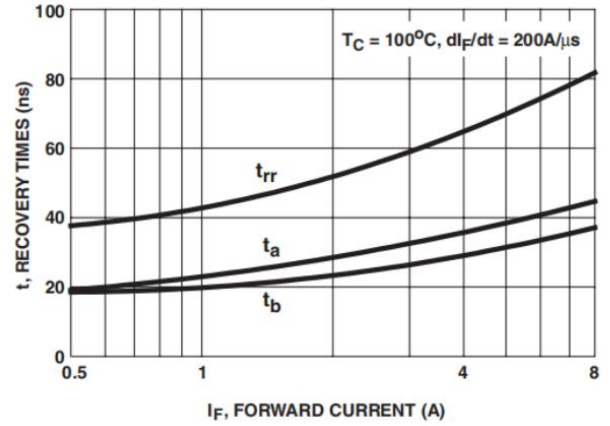


FIGURE 4. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

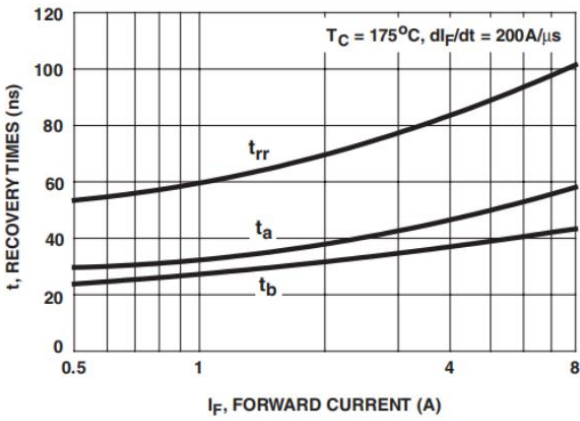


FIGURE 5. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

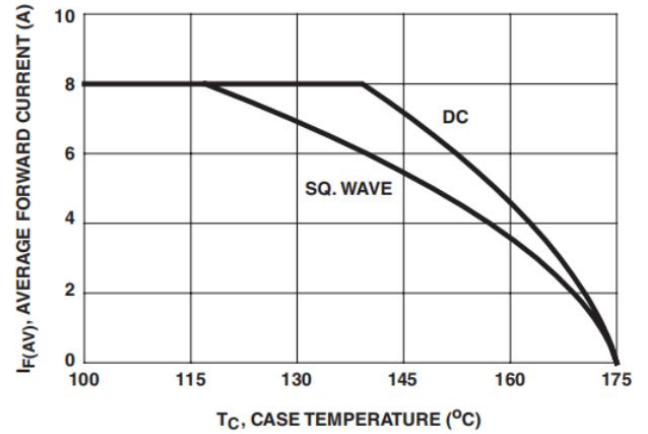


FIGURE 6. CURRENT DERATING CURVE

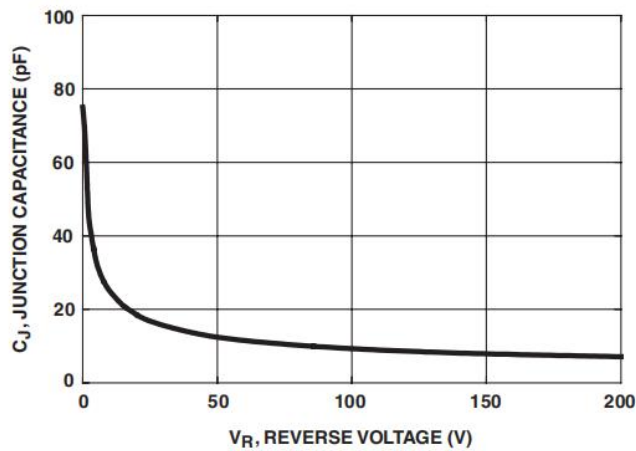
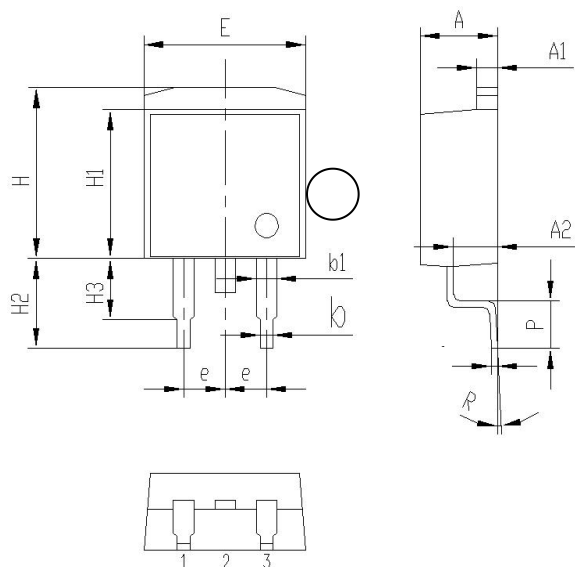


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

Package Information
TO-263 PACKAGE
基本尺寸


Symbol	单位 mm		
	Min	Nom	Max
A	4.40	4.6	4.80
A1	1.17	1.27	1.37
A2	2.40	2.6	2.80
b	0.60	0.8	1.00
b1	1.05	1.25	1.45
c	0.28	0.38	0.48
e	2.34	2.54	2.74
E	9.9	10.1	10.3
H	9.90	10.1	10.3
H1	8.50	8.7	8.90
H2	4.80	5.00	5.20
H3	2.60	2.8	3.00
R	0°	3°	6°
P	2.40	2.70	3.00

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